

74LVC3G06

Triple inverter with open-drain output

Rev. 05 — 21 May 2007

Product data sheet

1. General description

The 74LVC3G06 provides three inverting buffers.

The output of this device is an open drain and can be connected to other open-drain outputs to implement active-LOW wired-OR or active-HIGH wired-AND functions.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment.

Schmitt trigger action at all inputs makes the circuit tolerant for slower input rise and fall time.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V)
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- -24 mA output drive ($V_{CC} = 3.0$ V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package	Temperature range	Name	Description	Version
74LVC3G06DP		−40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74LVC3G06DC		−40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74LVC3G06GT		−40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm	SOT833-1
74LVC3G06GM		−40 °C to +125 °C	XQFN8	plastic extremely thin quad flat package; no leads; 8 terminals; body 1.6 × 1.6 × 0.5 mm	SOT902-1

4. Marking

Table 2. Marking

Type number	Marking code
74LVC3G06DP	V06
74LVC3G06DC	V06
74LVC3G06GT	V06
74LVC3G06GM	V06

5. Functional diagram

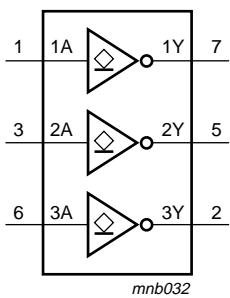


Fig 1. Logic symbol

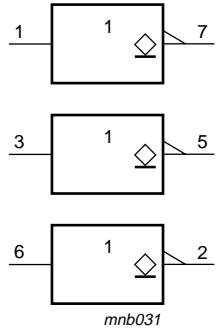


Fig 2. IEC logic symbol

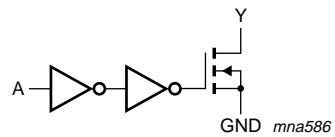


Fig 3. Logic diagram (one driver)

6. Pinning information

6.1 Pinning

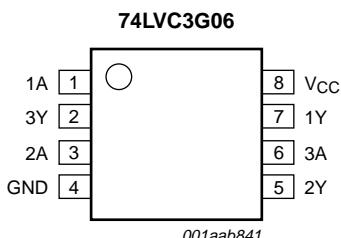


Fig 4. Pin configuration SOT505-2 (TSSOP8) and SOT765-1 (VSSOP8)

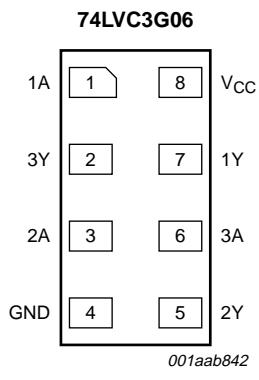


Fig 5. Pin configuration SOT833-1 (XSON8)

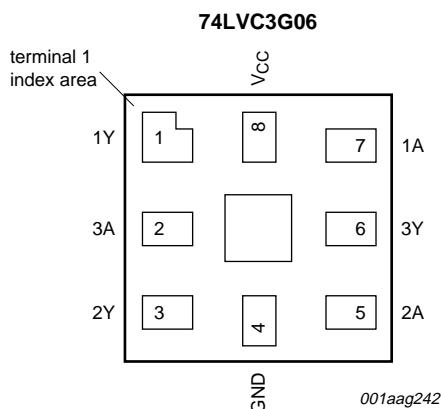


Fig 6. Pin configuration SOT902-1 (XQFN8)

6.2 Pin description

Table 3. Pin description

Symbol	Pin			Description
		SOT505-2, SOT765-1 and SOT833-1	SOT902-1	
1A	1		7	data input
3Y	2		6	data output
2A	3		5	data input
GND	4		4	ground (0 V)
2Y	5		3	data output

Table 3. Pin description ...continued

Symbol	Pin	Description	
		SOT505-2, SOT765-1 and SOT833-1	SOT902-1
3A	6	2	data input
1Y	7	1	data output
V _{CC}	8	8	supply voltage

7. Functional description

Table 4. Function table^[1]

Input nA	Output nY
L	Z
H	L

[1] H = HIGH voltage level;
 L = LOW voltage level;
 Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
V _I	input voltage		[1]	-0.5	+6.5
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
V _O	output voltage	Active mode	[1]	-0.5	+6.5
		Power-down mode	[1][2]	-0.5	+6.5
I _O	output current	V _O = 0 V to 6.5 V	-	50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
T _{STG}	storage temperature		-65	+150	°C
P _{TOT}	total power dissipation	T _{AMB} = -40 °C to +125 °C	[3]	-	250
					mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When V_{CC} = 0 V (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For TSSOP8 and VSSOP8 packages: above 110 °C the value of P_{TOT} derates linearly with 8.0 mW/K.

For XSON8 and XQFN8 packages: above 45 °C the value of P_{TOT} derates linearly with 2.4 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CC}	supply voltage		1.65	-	5.5	V
V _I	input voltage		0	-	5.5	V
V _O	output voltage	Active mode	0	-	5.5	V
		Power-down mode; V _{CC} = 0 V	0	-	5.5	V
T _{amb}	ambient temperature		-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V _{CC} = 1.65 V to 2.7 V	-	-	20	ns/V
		V _{CC} = 2.7 V to 5.5 V	-	-	10	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
T_{amb} = -40 °C to +85 °C [1]							
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}	-	-	V	
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	V	
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	V	
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}	-	-	V	
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	0.35 × V _{CC}	V	
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V	
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	V	
		V _{CC} = 4.5 V to 5.5 V	-	-	0.3 × V _{CC}	V	
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}					
		I _O = 100 μA; V _{CC} = 1.65 V to 5.5 V	-	-	0.10	V	
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.45	V	
		I _O = 8 mA; V _{CC} = 2.3 V	-	-	0.30	V	
		I _O = 12 mA; V _{CC} = 2.7 V	-	-	0.40	V	
		I _O = 24 mA; V _{CC} = 3.0 V	-	-	0.55	V	
		I _O = 32 mA; V _{CC} = 4.5 V	-	-	0.55	V	
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	[2]	-	±0.1	±5	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 5.5 V	-	±0.1	±10	μA	
I _{OFF}	power-off leakage current	V _I or V _O = 5.5 V; V _{CC} = 0 V	-	±0.1	±10	μA	
I _{CC}	supply current	V _I = 5.5 V or GND; I _O = 0 A; V _{CC} = 1.65 V to 5.5 V	-	0.1	10	μA	
ΔI _{CC}	additional supply current	per pin; V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 2.3 V to 5.5 V	[2]	-	5	500	μA
C _I	input capacitance		-	2.5	-	pF	

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = -40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	V
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	0.3 × V _{CC}	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 100 µA; V _{CC} = 1.65 V to 5.5 V	-	-	0.10	V
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.70	V
		I _O = 8 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 12 mA; V _{CC} = 2.7 V	-	-	0.60	V
		I _O = 24 mA; V _{CC} = 3.0 V	-	-	0.80	V
		I _O = 32 mA; V _{CC} = 4.5 V	-	-	0.80	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	±20	µA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±10	µA
I _{OFF}	power-off leakage current	V _I or V _O = 5.5 V; V _{CC} = 0 V	-	-	±20	µA
I _{CC}	supply current	V _I = 5.5 V or GND; I _O = 0 A; V _{CC} = 1.65 V to 5.5 V	-	-	40	µA
ΔI _{CC}	additional supply current	per pin; V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 2.3 V to 5.5 V	-	-	5000	µA

[1] All typical values are measured at T_{amb} = 25 °C.[2] These typical values are measured at V_{CC} = 3.3 V.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit	
			Min	Typ ^[1]	Max	Min	Max		
t_{pd}	propagation delay nA to nY; see Figure 7	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ $V_{CC} = 2.7 \text{ V}$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[2]	1.0	2.6	6.5	1.0	8.2	ns
				0.5	1.6	3.9	0.5	4.9	ns
				1.0	2.2	4.2	1.0	5.3	ns
				0.5	2.0	3.4	0.5	4.3	ns
				0.5	1.4	2.9	0.5	3.7	ns
C_{PD}	power dissipation capacitance	$V_I = \text{GND to } V_{CC}; V_{CC} = 3.3 \text{ V}$	[3]	-	5.9	-	-	-	pF

[1] Typical values are measured at $T_{amb} = 25 \text{ }^{\circ}\text{C}$ and $V_{CC} = 1.8 \text{ V}, 2.5 \text{ V}, 2.7 \text{ V}, 3.3 \text{ V}$ and 5.0 V respectively.

[2] t_{pd} is the same as t_{PLZ} and t_{PZL} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o)$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

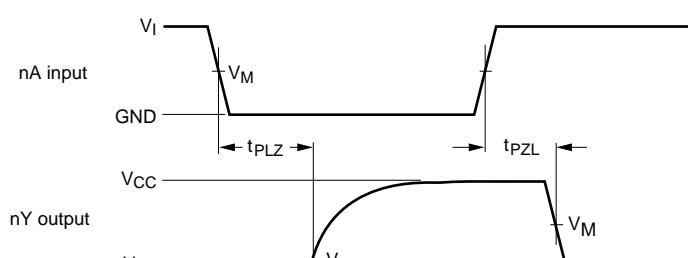
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\sum(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms



mnb033

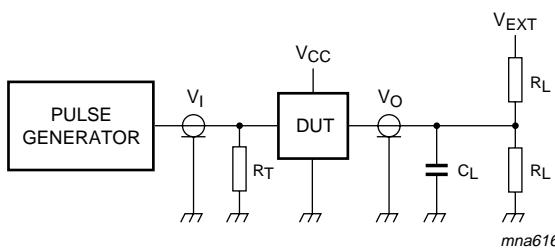
Measurement points are given in [Table 9](#).

V_{OL} is the typical output voltage drop that occurs with the output load.

Fig 7. The input (nA) to output (nY) propagation delays

Table 9. Measurement points

Supply voltage	Input	Output	
V _{CC}	V _M	V _M	V _X
1.65 V to 1.95 V	0.5 × V _{CC}	0.5 × V _{CC}	V _{OL} + 0.15 V
2.3 V to 2.7 V	0.5 × V _{CC}	0.5 × V _{CC}	V _{OL} + 0.15 V
2.7 V	1.5 V	1.5 V	V _{OL} + 0.3 V
3.0 V to 3.6 V	1.5 V	1.5 V	V _{OL} + 0.3 V
4.5 V to 5.5 V	0.5 × V _{CC}	0.5 × V _{CC}	V _{OL} + 0.3 V



Test data is given in [Table 10](#).

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig 8. Load circuitry for switching times

Table 10. Test data

Supply voltage	Input	Load		V _{EXT}	
V _{CC}	V _I	t _r , t _f	C _L	R _L	t _{PZL} , t _{PLZ}
1.65 V to 1.95 V	V _{CC}	≤ 2.0 ns	30 pF	1 kΩ	2 × V _{CC}
2.3 V to 2.7 V	V _{CC}	≤ 2.0 ns	30 pF	500 Ω	2 × V _{CC}
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	6 V
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	6 V
4.5 V to 5.5 V	V _{CC}	≤ 2.5 ns	50 pF	500 Ω	2 × V _{CC}

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

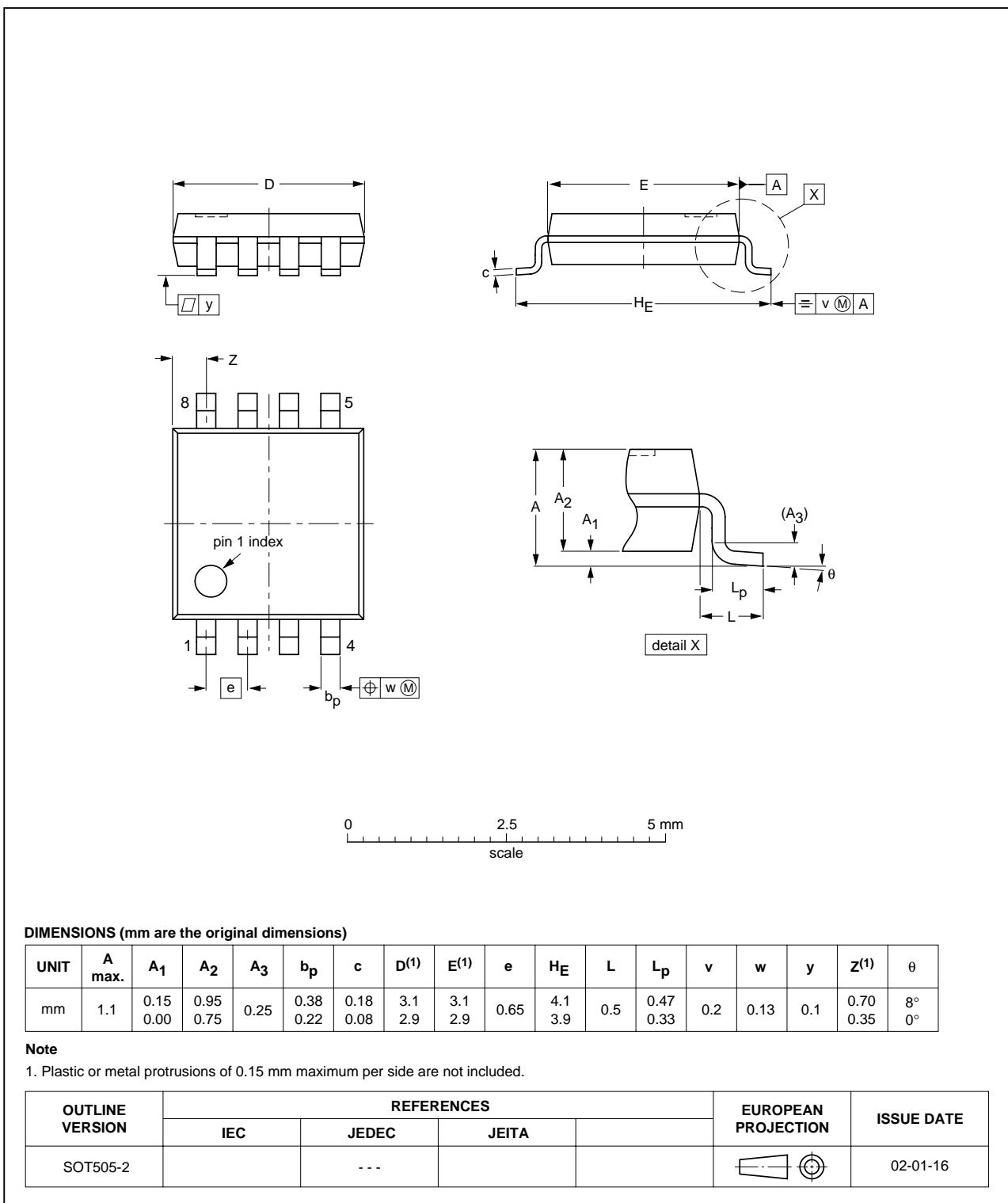
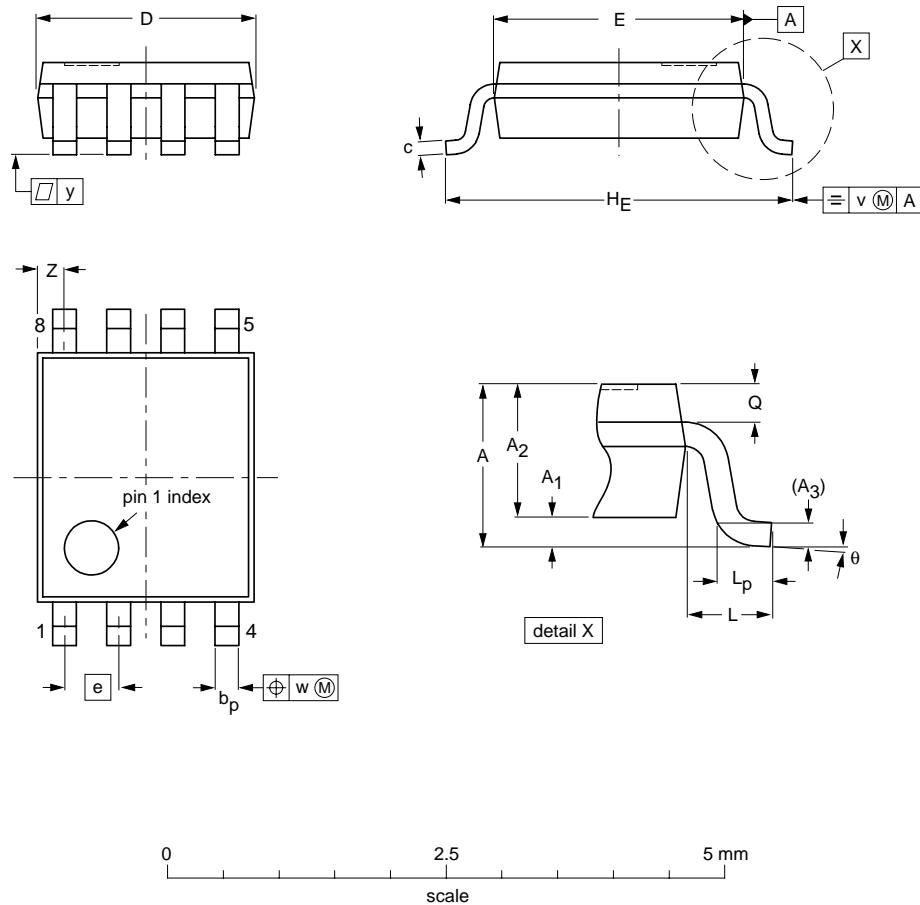


Fig 9. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

**DIMENSIONS (mm are the original dimensions)**

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽²⁾	e	H _E	L	L _p	Q	v	w	y	Z ⁽¹⁾	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

Notes

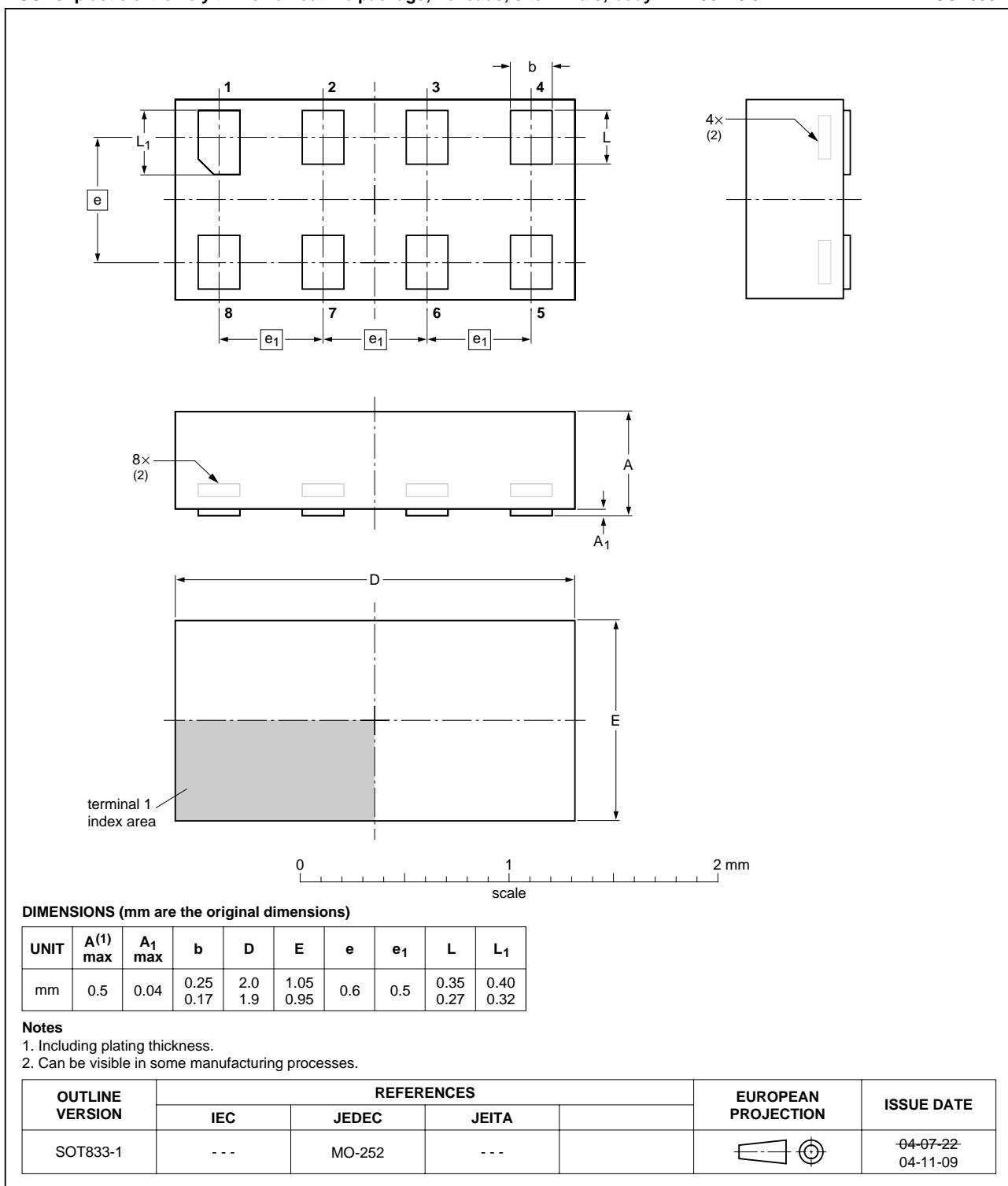
1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT765-1		MO-187				02-06-07

Fig 10. Package outline SOT765-1 (VSSOP8)

XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 1 x 1.95 x 0.5 mm

SOT833-1

**Fig 11. Package outline SOT833-1 (XSON8)**

XQFN8: plastic extremely thin quad flat package; no leads; 8 terminals; body 1.6 x 1.6 x 0.5 mm

SOT902-1

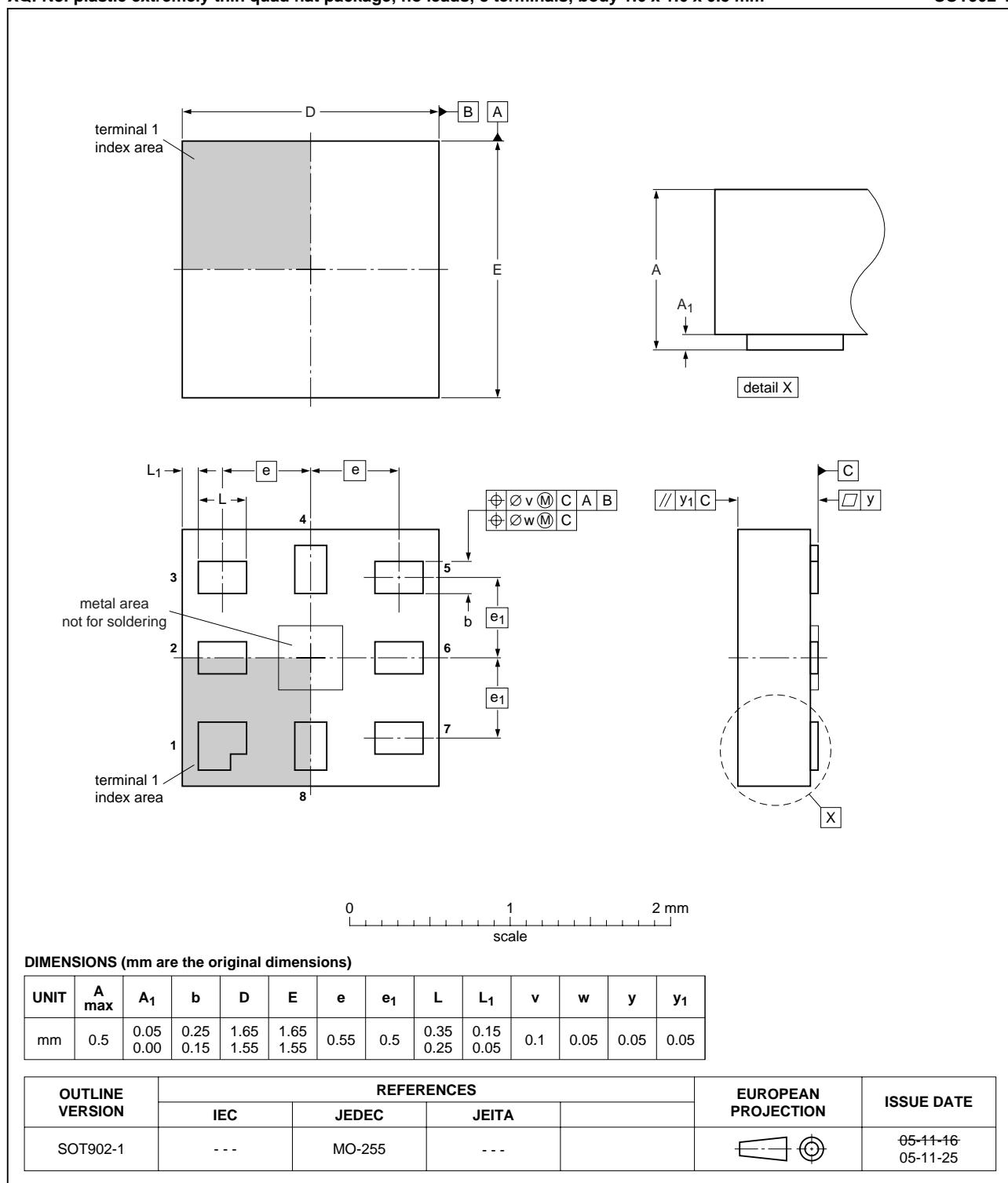


Fig 12. Package outline SOT902-1 (XQFN8)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC3G06_5	20070521	Product data sheet	-	74LVC3G06_4
Modifications:	<ul style="list-style-type: none"> The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. Added type number 74LVC3G06GM (XQFN8/SOT902-1 package). <u>Section 10 "Static characteristics":</u> Changed: Conditions for input leakage and supply current. 			
74LVC3G06_4	20060302	Product data sheet	-	74LVC3G06_3
74LVC3G06_3	20050201	Product data sheet	-	74LVC3G06_2
74LVC3G06_2	20041021	Product data sheet	-	74LVC3G06_1
74LVC3G06_1	20040607	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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